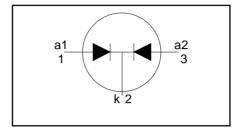
Rectifier diodes Schottky barrier

PBYR3045WT series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 40 \text{ V}/45 \text{ V}$$

$$I_{O(AV)} = 30 \text{ A}$$

$$I_{FSM} = 300 \text{ A}$$

$$V_F \le 0.6 \text{ V}$$

GENERAL DESCRIPTION

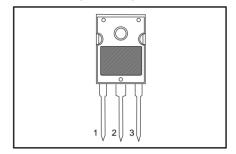
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR3045WT series is supplied in the conventional leaded SOT429 (TO247) package.

PINNING

PIN	DESCRIPTION	
1	anode 1 (a)	
2	cathode (k)	
3	anode 2 (a)	
tab	cathode	

SOT429 (TO247)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MIN. MAX.		UNIT
		PBYR30		40WT	45WT	
V_{RRM}	Peak repetitive reverse voltage		-	40	45	V
V_{RWM}	Working peak reverse voltage		-	40	45	V
V_R	Continuous reverse voltage	$T_{mb} \le 107 ^{\circ}C$	-	40	45	V
I _{O(AV)}	Average rectified output current (both diodes conducting)	square wave; δ = 0.5; $T_{mb} \le 124$ °C	-	30		А
I_{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \le 124$ °C	-	3	0	Α
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$	- -	300 330		A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{i max}	-	2	2	Α
T _j	Operating junction temperature	, max	-	15	50	°C
T _{stg}	Storage temperature		- 65	175		°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-a}	to mounting base	per diode both diodes in free air	1 1 1	- - 45	1.6 1.2 -	K/W K/W K/W

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ELECTRICAL CHARACTERISTICS

characteristics are per diode at $T_j = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage per diode	$I_{\rm F} = 20 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.58	0.6	V
'		$I_F = 20 \text{ A}; T_i = 125^{\circ}\text{C}$ $I_F = 30 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.69	0.72	V
		$I_{\rm F} = 30 {\rm A}^{-1}$	-	0.71	0.76	V
I _R	Reverse current per diode	$V_R = V_{RWM}$	-	0.12	1.5	mΑ
	·	$V_{R} = V_{RWM}$; $T_{i} = 100^{\circ}C$	-	15	30	mΑ
C _d	Junction capacitance	$V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_i = 25 \text{ °C to } 125 \text{ °C}$	-	450	-	pF

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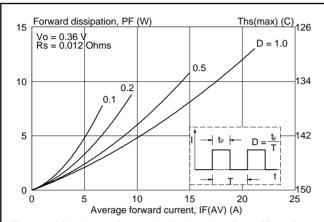


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$.

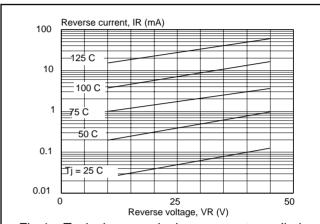


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

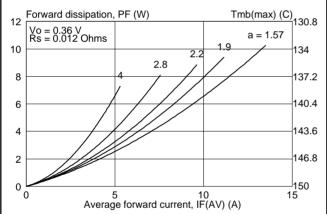


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.

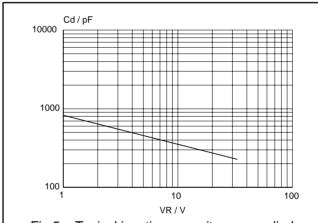


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125°C.

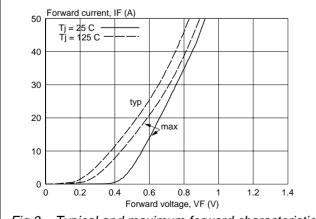


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

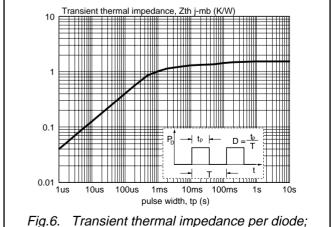
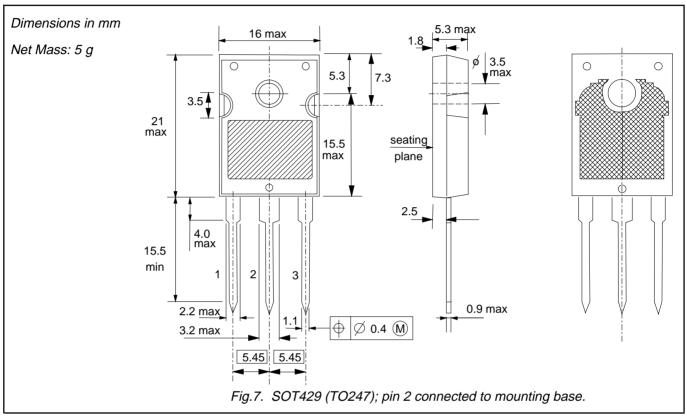


Fig.6. Transient thermal impedance per diode; $Z_{th j-mb} = f(t_p)$.

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MECHANICAL DATA



- Refer to mounting instructions for SOT429 envelope.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

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PBYR3045WT series

DEFINITIONS

Data sheet status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la		
Product specification This data sheet contains final product specifications.		
Limiting values		

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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